

detecting at least one defect on the main surface of said mask blank and obtaining defect analysis data including at least the kind of said defect and the position of the defect relative to said position measuring marks;

comparing the obtained defect position with the relative position of the mask pattern that is to be formed on the mask blank so as to select a mask pattern arranging position relative to the mask blank; and

measuring the position measuring marks to calculate the light exposure position and applying an exposure treatment to the selected position.

11. (Amended) The pattern forming method according to claim 9, wherein: said mask blank comprises a transparent substrate and a light shielding film formed on said transparent substrate and is used for fabrication of a photomask that is exposed as a mask with transmissive exposure;

said defect includes a black type defect and a white type defect; and the pattern arranging position is selected such that said black type defect is buried in a light shielding film pattern, and said white type defect is exposed to a pattern opening that is not covered with said light shielding pattern.

12. (Amended) The pattern forming method according to claim 9, wherein: said mask blank comprises a supporting substrate, a reflecting film formed on said supporting substrate, and a light shielding film formed on said reflecting film;

said at least one defect comprises at least one defect that lowers the reflectivity; and

the pattern arranging position is selected such that at least one of said defect lowering the reflectivity is buried in a non-reflecting pattern and at least another of said

defect lowering the reflectivity is positioned on an opening that is not covered with a light shielding film pattern.

21. (New) The pattern forming method according to claim 9, wherein:

said mask blank comprises a supporting substrate and a light reflecting film on said supporting substrate, or comprises a supporting substrate, a light reflecting film on said supporting substrate, and a light shielding film formed on said reflecting film and is used for fabrication of a photomask that is exposed as a reflection mask;

said defect comprises a defect that is located in said light reflecting film and lowers the reflectivity, a defect that is located in said light shielding film and lowers the shielding and be a defect in reflective pattern, and a defect that is located on a surface or bottom of said light shielding film and that is remained as a defect and lowers the reflectivity and be a defect in reflective pattern; and

the pattern arranging position is selected such that said defect that is located in said light reflecting film is positioned in a non-reflecting pattern, and said defect that is located in said light shielding film and lowers the shielding is positioned in reflective pattern and said defect that is located surface or bottom of said light shielding film is positioned in a non-reflecting pattern; or a pattern arranging position for every defect is selected in a non-reflection pattern that is located in the middle position of said non-reflection pattern and be repaired by shielding material.

REMARKS

By this Amendment, Applicant amends claims 9, 11, and 12 to more clearly recite the features of the present invention and adds claim 21 to protect additional aspects of the invention. Applicant submits that no new matter has been introduced. In

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